MASWSS0204



GaAs SPDT 2.7 V High Power Switch DC - 3.0 GHz

Rev. V3

Features

- Low Voltage Operation: 2.7 V
- High IP3: +56 dBm
- Low Insertion Loss: 0.30 dB at 1 GHz
- High Isolation: 25 dB at 1 GHz
- 0.5 micron GaAs PHEMT Process
- Lead-Free SC70 Package
- Halogen-Free "Green" Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of MASWSS0117

Description

The MASWSS0204 is a GaAs pHEMT MMIC single pole double throw (SPDT) high power switch in a low cost SC70 six lead package. The MASWSS0204 is ideally suited for applications where high power, low control voltage, low insertion loss, high isolation, small size and low cost are required.

Typical applications are for CDMA handset systems that connect separate transceiver and/or GPS functions to a common antenna, as well as other related handset and general purpose applications. The MASWSS0204 can be used in all systems operating up to 3 GHz requiring high power at low control voltage.

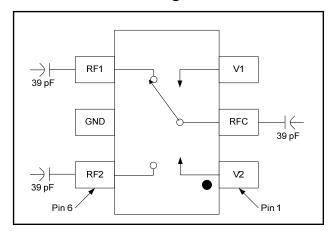
The MASWSS0204 is fabricated using a 0.5 micron gate length GaAs pHEMT process. The process features full passivation for performance and reliability.

Ordering Information 1,2

Part Number	Package		
MASWSS0204	Bulk Packaging		
MASWSS0204TR-3000	3000 piece reel		
MASWSS0204SMB	Sample Test Board		

- 1. Reference Application Note M513 for reel size information.
- 2. All sample boards include 5 loose parts.

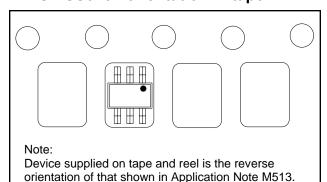
Functional Block Diagram



Pin Configuration

Pin No.	Pin Name	Description	
1	V2	Vcontrol 2	
2	RFC	RF Common	
3	V1	Vcontrol 1	
4	RF1	RF Port 1	
5	GND	RF Ground	
6	RF2	RF Port 2	

MASWSS0204 orientation in tape



^{*} Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

MASWSS0204



GaAs SPDT 2.7 V High Power Switch DC - 3.0 GHz

Rev. V3

Electrical Specifications: $T_A = 25$ °C, Vc = 0 V/2.7 V, $Z_0 = 50 \Omega^3$

Parameter	Test Conditions	Units	Min.	Тур.	Max.
Insertion Loss ⁴	DC - 1 GHz 1 - 2 GHz 2 - 3 GHz			0.30 0.35 0.35	0.65 — —
Isolation	DC - 1 GHz 1 - 2 GHz 2 - 3 GHz	dB	23 _	25 19 15	
Return Loss	DC - 3 GHz	dB	_	20	_
IP3	825 MHz Two Tone, +24 dBm Total Pin, 5 MHz Spacing		_	56	_
Cross Modulation	For Cell Band: Two-tone signal input: $T_X1 = +22 \text{ dBm } @ 820 \text{ MHz}, \\ T_X2 = +22 \text{ dBm } @ 821 \text{ MHz}, \\ R_X \text{ interfere = -23 dBm } @ 869 \text{ MHz}.$	dBm	_	-99	_
	For PCS Band: Two-tone signal input: $T_X1 = +18$ dBm @ 1880 MHz, $T_X2 = +18$ dBm @ 1881 MHz, R_X interfere = -23 dBm @ 1960 MHz.	dBm	_	-94	_
P0.1dB	1 GHz	dBm	_	38	_
Trise, Tfall	10% to 90% RF, 90% to 10% RF	ns	_	70	_
Ton, Toff	50% control to 90% RF, 50% control to 10% RF	ns	_	100	_
Transients	In Band	mV	_	25	_
Control Current	V _C = 2.7 V	μΑ	_	5	20

^{3.} For positive voltage control, external DC blocking capacitors are required on all RF ports.

Absolute Maximum Ratings 5,6

Parameter	Absolute Maximum		
Input Power (0.5 - 3 GHz, 3 V Control)	+38 dBm		
Operating Voltage	+8.5 volts		
Operating Temperature	-40°C to +85°C		
Storage Temperature	-65°C to +150°C		

Exceeding any one or combination of these limits may cause permanent damage to this device.

Commitment to produce in volume is not guaranteed.

Truth Table 7,8,9

V1	V2	ANT-RF1	ANT - RF2
1	0	On	Off
0	1	Off	On

- 7. For positive voltage control, external DC blocking capacitors are required on all RF ports.
- Differential voltage, V(state 1) V(state 0), must be +2.7 V minimum, but must not exceed 8.5 V.
- 9. 0 = -5 V to +2.3 V, 1 = -2.3 V to +5 V.

^{4.} Insertion loss can be optimized by varying the DC blocking capacitor value, e.g. 1000 pF for 100 MHz - 1 GHz, 39 pF for 0.5 - 3 GHz.

M/A-COM Technology does not recommend sustained operation near these survivability limits.

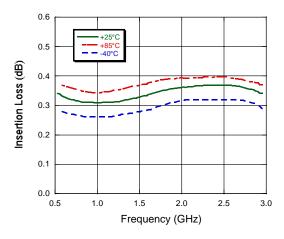


GaAs SPDT 2.7 V High Power Switch DC - 3.0 GHz

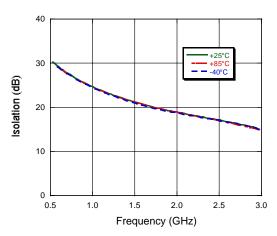
Rev. V3

Typical Performance Curves, 39 pF

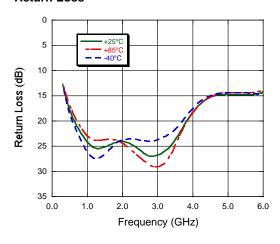
Insertion Loss



Isolation



Return Loss



Commitment to produce in volume is not guaranteed.

Qualification

Qualified to M/A-COM specification REL-201, Process Flow –2.

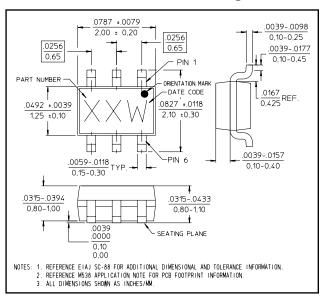
Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

Lead-Free SC70 Plastic Package[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.

Meets JEDEC moisture sensitivity level 1 requirements. Plating is 100% matte tin over copper.

3

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are

typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available.

• India Tel:

• North America Tel: 800.366.2266 • Europe Tel: +353.21.244.6400

• India Tel: +91.80.43537383

• China Tel: +86.21.2407.1588

Visit www.macomtech.com for additional data sheets and product information.